Silicon N-Channel MOS FET

HITACHI

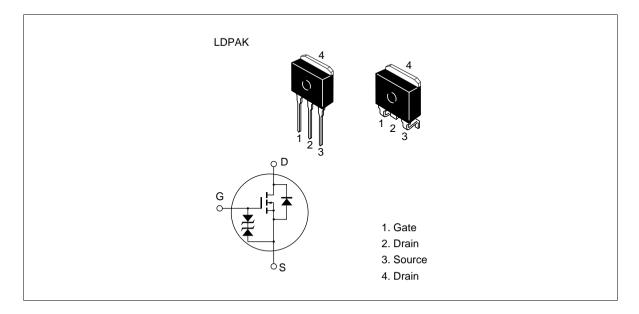
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1540	V _{DSS}	450	V
	2SK1541		500	
Gate to source voltage		V_{GSS}	±30	V
Drain current		I _D	7	А
Drain peak current		l _{D(pulse)} *1	28	A
Body to drain diode reverse	e drain current	I _{DR}	7	A
Channel dissipation		Pch*2	60	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

Note

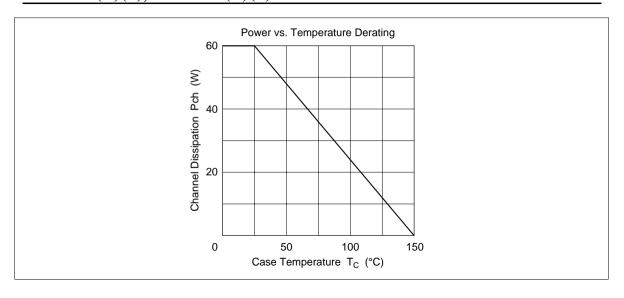
- 1. PW \leq 10 μ s, duty cycle \leq 1%
- 2. Value at $T_c = 25^{\circ}C$

Electrical Characteristics ($Ta = 25^{\circ}C$)

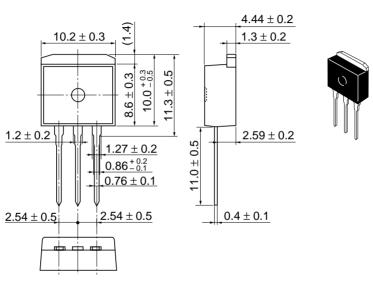
Item		Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source	2SK1540	$V_{(BR)DSS}$	450	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
breakdown voltage	2SK1541	-	500	_			
Gate to source breakdown voltage		$V_{(BR)GSS}$	±30	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current		I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage	2SK1540	I _{DSS}	_	_	250	μΑ	$V_{DS} = 360 \text{ V}, V_{GS} = 0$
drain current	2SK1541	-					$V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source cutoff	voltage	$V_{\rm GS(off)}$	2.0	_	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static Drain to source	2SK1540	R _{DS(on)}	_	0.6	0.8	Ω	$I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
on state resistance	2SK1541	-	_	0.7	0.9	_	
Forward transfer adm	nittance	yfs	4.0	6.5	_	S	$I_D = 4 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance		Ciss	_	1050	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance		Coss	_	280	_	pF	f = 1 MHz
Reverse transfer capacitance		Crss	_	40	_	pF	_
Turn-on delay time		t _{d(on)}	_	15	_	ns	$I_D = 4 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time		t _r	_	55	_	ns	$R_L = 7.5 \Omega$
Turn-off delay time		t _{d(off)}	_	95	_	ns	_
Fall time		t _f	_	40	_	ns	_
Body to drain diode for voltage	orward	V_{DF}		0.95		V	$I_F = 7 \text{ A}, V_{GS} = 0$
Body to drain diode recovery time	everse	t _{rr}	_	320	_	ns	$I_F = 7 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A/}\mu\text{s}$

Note 1. Pulse test

See characteristic curves of 2SK1157, 2SK1158.



Unit: mm



Hitachi Code	LDPAK (L)				
JEDEC					
EIAJ					
Weight (reference value)	1.4 g				

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